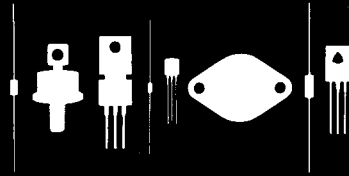


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145 Adams Avenue
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2N5056
2N5057

PNP SILICON SWITCHING TRANSISTOR

JEDEC TO-18 CASE*

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5056, 2N5057 types are Silicon PNP Saturated Switching Transistors designed for high speed switching applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>		<u>UNIT</u>
Collector-Base Voltage	V_{CB0}	15	V
Collector-Emitter Voltage	V_{CE0}	15	V
Emitter-Base Voltage	V_{EB0}	4.5	V
Collector Current	I_C	200	mA
Power Dissipation	P_D	0.5	W
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +200	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>2N5056</u>		<u>2N5057</u>		<u>UNIT</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
I_{CES}	$V_{CE}=10\text{V}$		50		50	nA
I_{CES}	$V_{CE}=10\text{V}, T_A=125^{\circ}\text{C}$		10		10	μA
BV_{CB0}	$I_C=10\mu\text{A}$	15		15		V
BV_{CES}	$I_C=10\mu\text{A}$	15		15		V
BV_{CE0}	$I_C=10\text{mA}$	15		15		V
BV_{EB0}	$I_E=100\mu\text{A}$	4.5		4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.13		0.13	V
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		0.19		0.19	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.45		0.45	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.92		0.92	V
$V_{BE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		1.15		1.15	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.5		1.5	V
h_{FE}	$V_{CE}=0.5\text{V}, I_C=1.0\text{mA}$	12		20		
h_{FE}	$V_{CE}=0.3\text{V}, I_C=10\text{mA}$	20		30		
h_{FE}	$V_{CE}=0.5\text{V}, I_C=30\text{mA}$	30	100	40	100	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	20		30		
f_T	$V_{CE}=10\text{V}, I_C=30\text{mA}, f=100\text{MHz}$	600		800		MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0$		4.5		4.5	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0$		6.0		6.0	pF
t_{on}	$V_{CC}=3.0\text{V}, I_C=30\text{mA}, I_{B1}=3.0\text{mA}$		20		20	ns
t_{off}	$V_{CC}=3.0\text{V}, I_C=30\text{mA}, I_{B1}=I_{B2}=3.0\text{mA}$		35		35	ns
t_s	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=10\text{mA}$		30		30	ns

* Conforms to JEDEC To-18 Case except MIN. CAN HEIGHT is .115 inches (instead of .170)